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# 2SK2114, 2SK2115

Silicon N-Channel MOS FET

# HITACHI

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## Application

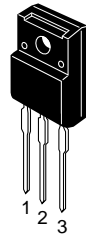
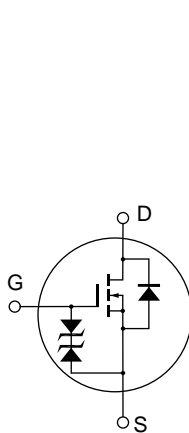
High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for Switching regulator

## Outline

TO-220CFM



1. Gate
2. Drain
3. Source

## 2SK2114, 2SK2115

### Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK2114	$V_{DSS}$	450	V
	2SK2115	$V_{DSS}$	500	
Gate to source voltage		$V_{GSS}$	±30	V
Drain current		$I_D$	5	A
Drain peak current		$I_{D(pulse)}^{*1}$	20	A
Body to drain diode reverse drain current		$I_{DR}$	5	A
Channel dissipation		$P_{ch}^{*2}$	35	W
Channel temperature		$T_{ch}$	150	°C
Storage temperature		$T_{stg}$	-55 to +150	°C

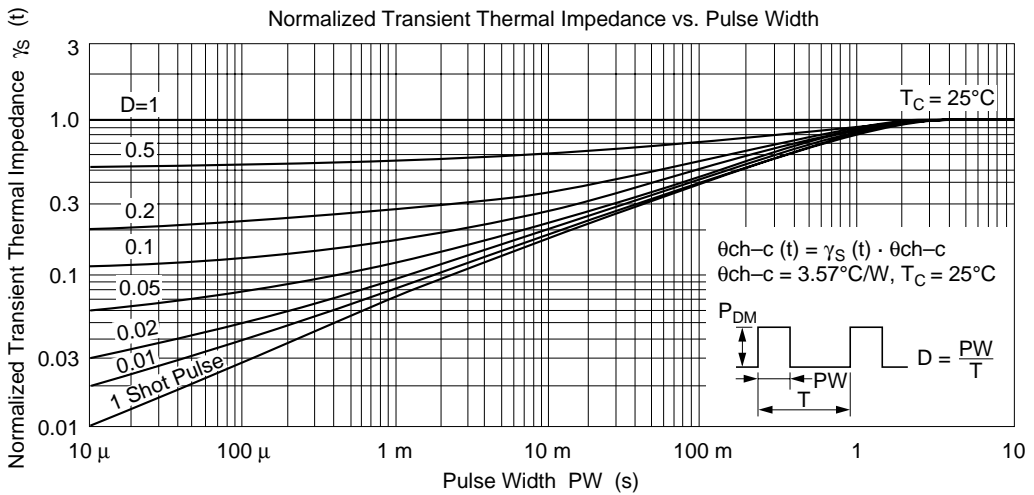
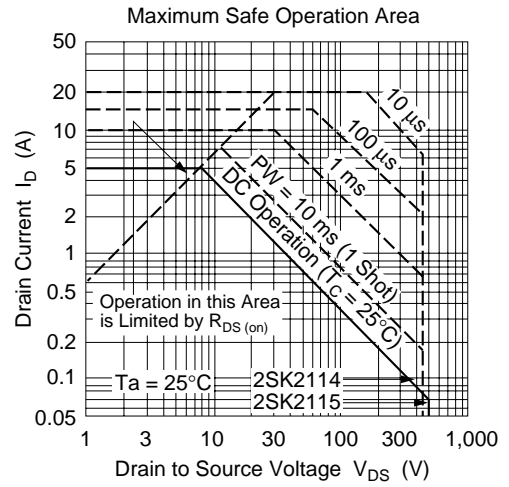
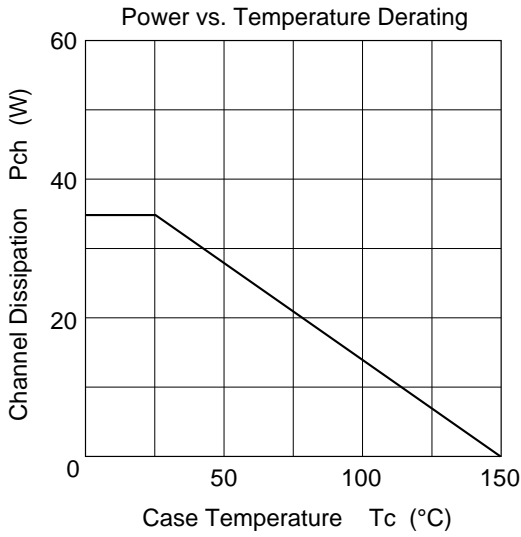
- Notes 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$   
2. Value at  $T_c = 25^\circ C$

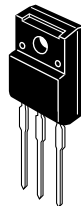
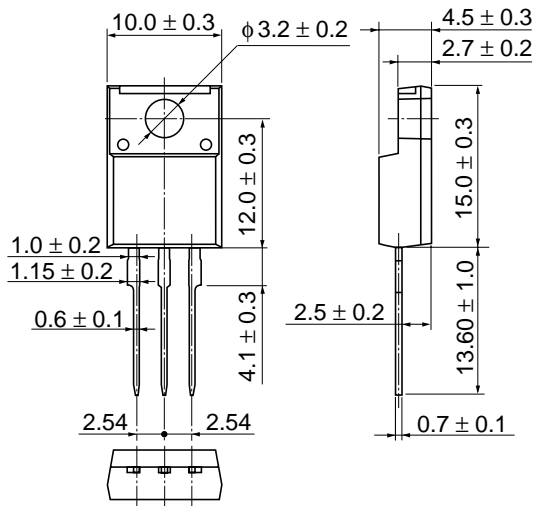
**Electrical Characteristics (Ta = 25°C)**

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK2114 2SK2115	$V_{(BR)DSS}$	450 500	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \text{ } \mu\text{A}, V_{DS} = 0$
Gate to source leak current		$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	2SK2114 2SK2115	$I_{DSS}$	—	—	250	μA	$V_{DS} = 360 \text{ V}, V_{GS} = 0$ $V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	2SK2114 2SK2115	$R_{DS(on)}$	— —	1.0 1.2	1.4 1.5	Ω	$I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance		$ y_{fs} $	2.5	4.0	—	S	$I_D = 2.5 \text{ A}$ $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		$C_{iss}$	—	640	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance		$C_{oss}$	—	160	—	pF	$V_{GS} = 0$
Reverse transfer capacitance		$C_{rss}$	—	20	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time		$t_{d(on)}$	—	10	—	ns	$I_D = 2.5 \text{ A}$
Rise time		$t_r$	—	25	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time		$t_{d(off)}$	—	50	—	ns	$R_L = 12 \text{ } \Omega$
Fall time		$t_f$	—	30	—	ns	
Body to drain diode forward voltage		$V_{DF}$	—	0.95	—	V	$I_F = 5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time		$t_{rr}$	—	300	—	ns	$I_F = 5 \text{ A}, V_{GS} = 0,$ $di_F / dt = 100 \text{ A} / \mu\text{s}$

Note 1. Pulse Test

See characteristics curve of 2SK1155, 2SK1156.





Hitachi Code	TO-220CFM
JEDEC	—
EIAJ	—
Weight (reference value)	1.9 g

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